DIODE MODULE

DD(KD)100GB40/80



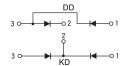
UL;E76102 (M)

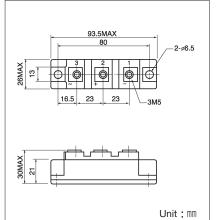
Power Diode Module **DD100GB** series are designed for various rectifier circuits. **DD100GB** has two diode chips connected in series and the mounting base is elctrically isolated from elements for simple heatsink construction. Wide voltage rating up to, 800V is avaiable for various input voltage.

- Isolated mounting base
- Two elements in a package for simple (single and three phase) bridge connections
- Highly reliable glass passivated chips
- High surge current capability

(Applications)

Various rectifiers, Battery chargers, DC motor drives





■Maximum Ratings

(Tj=25°C)

Symbol	ltone	Ratings		Linit
	Item	DD100GB40	DD100GB80	Unit
VRRM	Repetitive Peak Reverse Voltage	400	800	V
VRSM	Non-Repetitive Peak Reverse Voltage	480	960	V

Symbol	li li	Item Conditions		Ratings	Unit
IF (AV)	Average Forward Current		Single phase, half wave, 180° conduction, Tc: 115℃	100	Α
IF (RMS)	R.M.S. Forward Current		Single phase, half wave, 180° conduction, Tc: 115℃	155	Α
IFSM	Surge Forward Current		½ cycle, 50/60Hz, peak value, non-repetitive	1800/2000	Α
l²t	l²t		Value for one cycle of surge current	16500	A ² S
Tj	Junction Temperature			− 40∼ + 150	°C
Tstg	Storage Temperature			− 40∼ + 125	°C
Viso	Isolation Breakdown Voltage (R.M.S.)		A.C.1minute	2500	V
	Mounting	Mounting (M6)	Recommended Value 2.5~3.9 (25~40)	4.7 (48)	N·m
	Torque	Terminal (M5)	Recommended Value 1.5~2.5 (15~25)	2.7 (28)	(kgf·cm)
	Mass			170	g

■Electrical Characteristics

Symbol	Item	Item Conditions		Unit				
IRRM	Repetitive Peak Reverse Current, max.	at VDRM, single phase, half wave. Tj=150℃	30	mA				
VFM	Forward Voltage Drop, max.	Foward current 320A, Tj=25°C, Inst. measurement	1.25	V				
Rth (j-c)	Thermal Impedance, max.	Junction to case	0.30	°C/W				

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